

BSS138PS

60 V, 320 mA dual N-channel Trench MOSFET Rev. 1 — 2 November 2010

Product data sheet

Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V_{DS}	drain-source voltage	T _{amb} = 25 °C	-	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	-	±20	V
I _D	drain current	$T_{amb} = 25 ^{\circ}C;$ $V_{GS} = 10 ^{\circ}V$	[1] -	-	320	mA
R _{DSon}	drain-source on-state resistance	$T_j = 25 ^{\circ}\text{C};$ $V_{GS} = 10 \text{V};$ $I_D = 300 \text{mA}$	[2] -	0.9	1.6	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



^[2] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.01.$

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2. Pinning information

Table 2. Pinning

IUDIC Z.	1 1111111119			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1	6 5 4	D ₁ D ₂
3	D2	drain2		
4	S2	source2	0	
5	G2	gate2	∐1 ∐2 <u></u> 3	4141
6	D1	drain1		S_1 G_1 S_2 G_2
				msd901

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS138PS	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
BSS138PS	NZ*

^{[1] * =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	sistor				
V_{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D	drain current	V _{GS} = 10 V	<u>[1]</u>		
		T _{amb} = 25 °C	-	320	mA
		T _{amb} = 100 °C	-	200	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$	-	1.2	Α

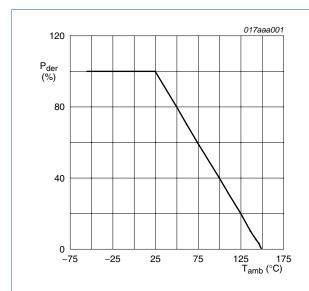
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 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

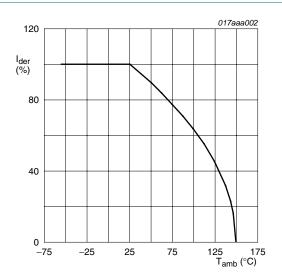
Parameter	Conditions	Min	Max	Unit
total power dissipation	$T_{amb} = 25 ^{\circ}C$	[2] _	280	mW
		[1] -	320	mW
	T _{sp} = 25 °C	-	960	mW
rain diode				
source current	T _{amb} = 25 °C	<u>[1]</u> -	290	mA
е				
total power dissipation	T _{amb} = 25 °C	[2] _	420	mW
junction temperature			150	°C
ambient temperature		-55	+150	°C
storage temperature		-65	+150	°C
	total power dissipation rain diode source current e total power dissipation junction temperature ambient temperature	total power dissipation $T_{amb} = 25 ^{\circ}\text{C}$ $T_{sp} = 25 ^{\circ}\text{C}$ rain diode source current $T_{amb} = 25 ^{\circ}\text{C}$ total power dissipation $T_{amb} = 25 ^{\circ}\text{C}$ junction temperature ambient temperature	total power dissipation $T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $ \underline{2} \ - \end{tabular} } \hfill & - \end{tabular} $ $T_{sp} = 25 ^{\circ}\text{C} \qquad \qquad - \end{tabular} $ $T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $1 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $ $total power dissipation \qquad T_{amb} = 25 ^{\circ}\text{C} \qquad \boxed{ \begin{tabular}{c} $2 \ - \end{tabular} } \hfill & - \end{tabular} $	total power dissipation $T_{amb} = 25 ^{\circ}\text{C} \qquad \qquad \begin{array}{ c c c c }\hline 12 & - & 280 \\\hline 11 & - & 320 \\\hline \hline T_{sp} = 25 ^{\circ}\text{C} \qquad & - & 960 \\\hline \end{array}$ $\begin{array}{ c c c c c }\hline \text{rain diode} & & & & \\\hline \text{source current} & T_{amb} = 25 ^{\circ}\text{C} & \boxed{11} & - & 290 \\\hline \textbf{e} & & & \\\hline \text{total power dissipation} & T_{amb} = 25 ^{\circ}\text{C} & \boxed{12} & - & 420 \\\hline \text{junction temperature} & & & 150 \\\hline \text{ambient temperature} & & & -55 & +150 \\\hline \end{array}$

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

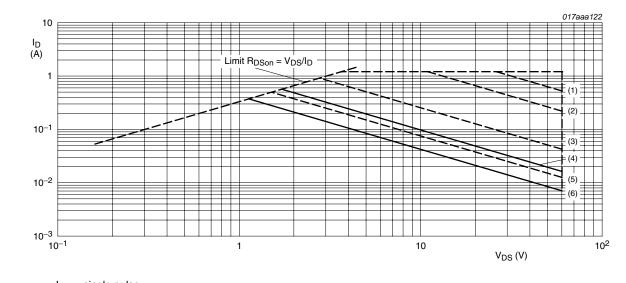
Fig 1. Normalized total power dissipation as a function of ambient temperature



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized continuous drain current as a function of ambient temperature

60 V, 320 mA dual N-channel Trench MOSFET



I_{DM} = single pulse

- (1) $t_p = 100 \mu s$
- (2) $t_p = 1 \text{ ms}$
- (3) $t_p = 10 \text{ ms}$
- (4) DC; $T_{sp} = 25 \,^{\circ}C$
- (5) $t_p = 100 \text{ ms}$
- (6) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 1 cm²

Fig 3. Per transistor: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	in free air	<u>[1]</u> -	390	445	K/W
		[2] _	340	390	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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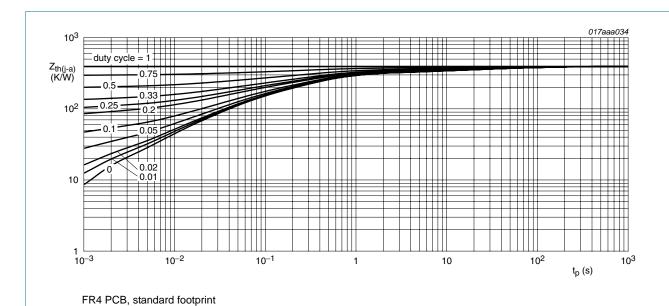


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

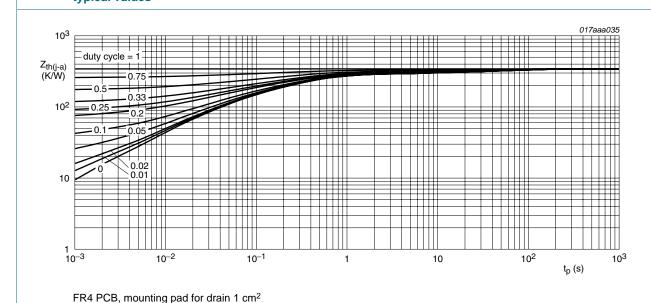


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 320 mA dual N-channel Trench MOSFET

7. Characteristics

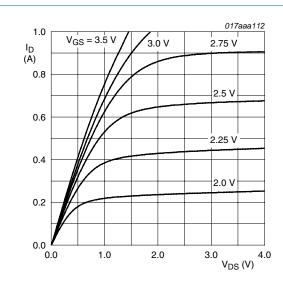
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}$	0.9	1.2	1.5	V
I _{DSS} c	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μΑ
		T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	100	nΑ
Doon	drain-source on-state resistance		[1]			
		$V_{GS} = 5 \text{ V}; I_D = 50 \text{ mA}$	-	1	2	Ω
		$V_{GS} = 10 \text{ V}; I_D = 300 \text{ mA}$	-	0.9	1.6	Ω
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}$	[1] -	700	-	mS
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge			0.72	8.0	nC
Q _{GS}	gate-source charge	$V_{DS} = 30 \text{ V};$	-	0.14	-	nC
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}$	-	0.24	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 10 \text{ V};$	-	38	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V};$	-	2	6	ns
t _r	rise time	$R_L = 250 \Omega;$	-	3	-	ns
t _{d(off)}	turn-off delay time	$-V_{GS} = 10 \text{ V};$ $R_G = 6 \Omega$	-	9	20	ns
t _f	fall time	_ •	-	4	-	ns
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}; V_{GS} = 0 \text{ V}$	0.47	0.75	1.1	V

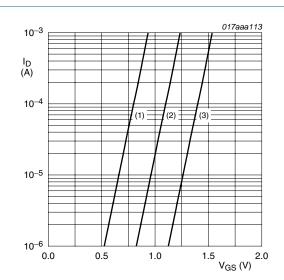
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.01.$

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 $T_{amb} = 25 \, ^{\circ}C$

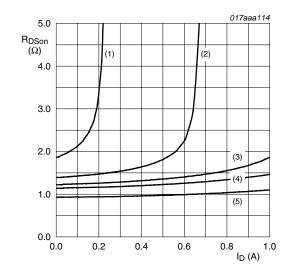
Fig 6. Per transistor: Output characteristics: drain current as a function of drain-source voltage; typical values



 T_{amb} = 25 °C; V_{DS} = 5 V

- (1) minimum values
- (2) typical values
- (3) maximum values

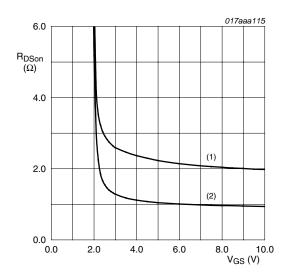
Fig 7. Per transistor: Sub-threshold drain current as a function of gate-source voltage



T_{amb} = 25 °C

- (1) $V_{GS} = 2 V$
- (2) $V_{GS} = 2.5 \text{ V}$
- (3) $V_{GS} = 3 V$
- (4) $V_{GS} = 3.5 \text{ V}$
- (5) $V_{GS} = 10 \text{ V}$

Fig 8. Per transistor: Drain-source on-state resistance as a function of drain current; typical values



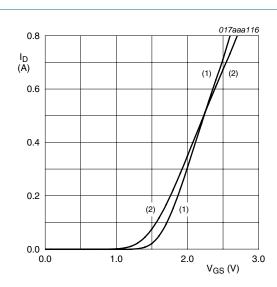
 $I_D = 300 \text{ mA}$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

Fig 9. Per transistor: Drain-source on-state resistance as a function of gate-source voltage; typical values

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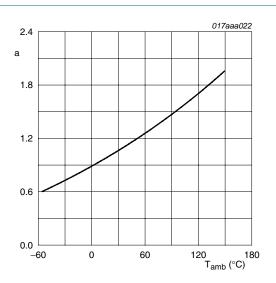


$$V_{DS} > I_D \times R_{DSon}$$

(1)
$$T_{amb} = 25 \,^{\circ}C$$

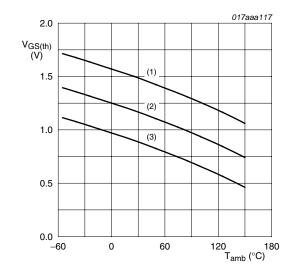
(2)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 10. Per transistor: Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

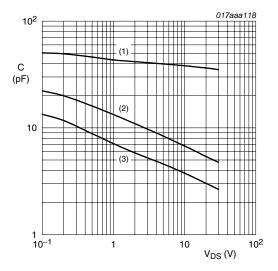
Fig 11. Per transistor: Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Per transistor: Gate-source threshold voltage as a function of ambient temperature

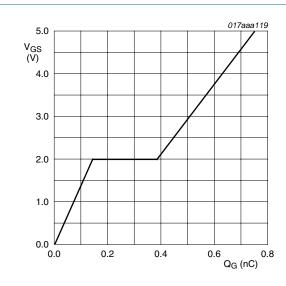


 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1) C_{iss}
- (2) Coss
- (3) C_{rss}

Fig 13. Per transistor: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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 I_D = 300 mA; V_{DS} = 30 V; T_{amb} = 25 °C

Fig 14. Per transistor: Gate-source voltage as a function of gate charge; typical values

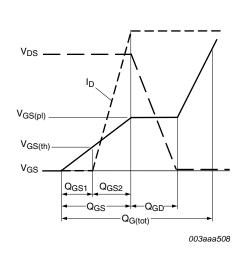
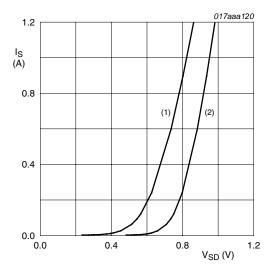


Fig 15. Per transistor: Gate charge waveform definitions



 $V_{GS} = 0 V$

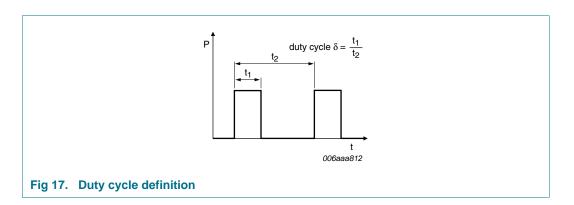
(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

Fig 16. Per transistor: Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 320 mA dual N-channel Trench MOSFET

9. Package outline

Plastic surface-mounted package; 6 leads

SOT363

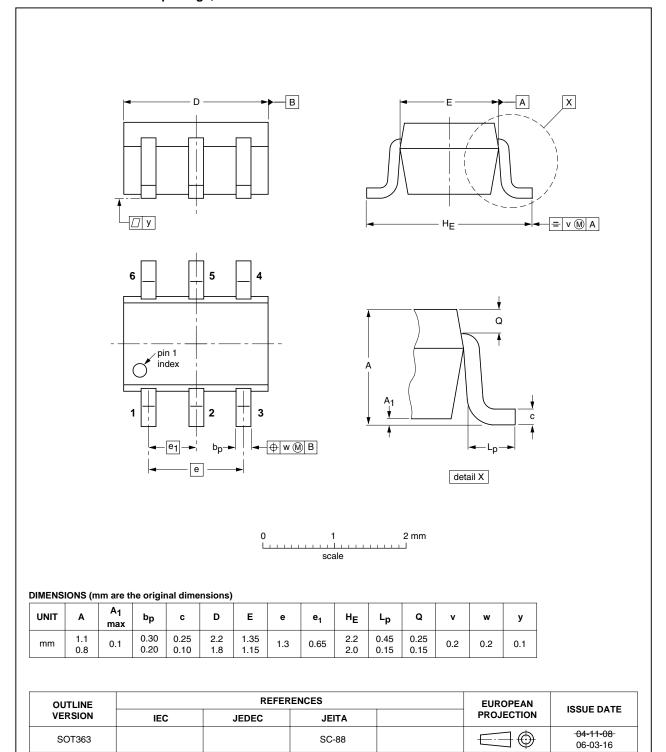
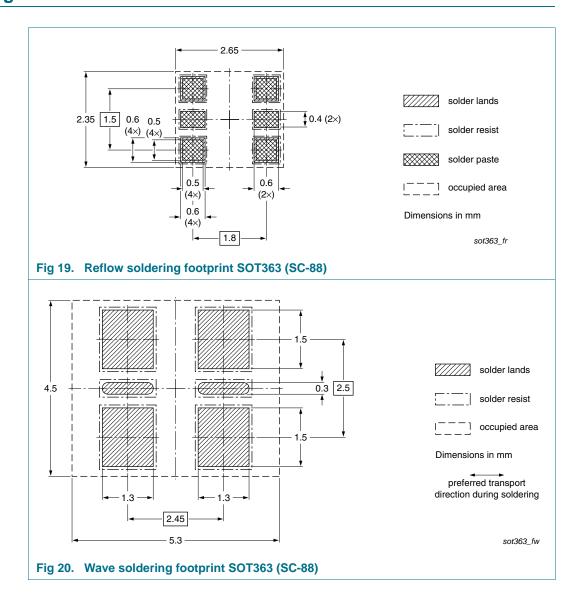


Fig 18. Package outline SOT363 (SC-88)

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60 V, 320 mA dual N-channel Trench MOSFET

10. Soldering



60 V, 320 mA dual N-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138PS v.1	20101102	Product data sheet	-	-

60 V, 320 mA dual N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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